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ABSTRACT OF THE DISCLOSURE

A process for crystal growth of III-V group compound semiconductor, which comprises pyrolyzing, in a gas phase, a material consisting of an organometallic compound and/or a hydride in the presence of an organic compound containing an oxygen atom-carbon atom direct bond, used as a dopant to grow a III-V group compound semiconductor crystal layer containing at least aluminum, of high electric resistance. Said process can grow a compound semiconductor layer of high electric resistance by the use of a dopant which enables the independent controls of oxygen concentration and aluminum concentration and which has a small effect of oxygen remaining.

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